2 6 200 C

RECEIVED

JUN 27 2003

Sheet ___ of __1

<u> </u>				TC 170	\ A				
(Rev. 5/92)		U.S. Department of Commerce			Atty. Docket No.		Serial No.		
Comparable to	Patent and Trademark Office				l				
Form PTO-1449)			82821		09/856,212			
	INFORMATION DISCLOSURE								
(Use several sheets if necessary)							_		
				Applicant NAKAMURA et al.					
				Filing Date May 18, 2001	Graup 1765				
U.S. PATENT DOCUMENTS									
*Examiner		,					Filing Date		
Initial	Document Number	Date	Name C		Class	Subclass	if Appropriate		
MS	4,437,922	03/20/1984	Bischoff et al.		()			
MS	4,944,834	07/31/1990	Tada et al.						
MS	6,036,776	03/14/2000	Kotooka et al.						
FOREIGN PATENT DOCUMENTS									
							Trans	lation	
	Document Number	Date	Name of Patentee		Class	Subclass	Yes	No	
w>	EP 0823497	02/11/1998	MEMC Electronic Materials, Inc.		/		×		
MS	EP 0866150	09/23/1998	Wacker Siltronic Gesellschaft fur		/	_	X		
	EP 0785298	06/26/2002	MEMC Electronic Materials, Inc.				*		
	JP 03-279290	12/10/1991	Osaka Titanium Co., Ltd.				X		
	JP 05-194076	08/03/1993	Kornatsu Denshi Kinzoku KK			_	X		
	JP 07-133187	05/23/1995	Kornatsu Electron Metals Co., Ltd.				*		
-	WO 98/45507	10/15/1998	MEMC Electronic Materials, Inc.				Υ		
MS	WO 98/45508	10/15/1998	MEMC Electronic Materials, Inc.			<u> </u>	X		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)									
MS NAKAMURA, KOZO et al.: "Formation process of grown-in defects in Czochralski grown silicon crystals" JOURNAL OF CRYSTAL GROWTH 180 (1997) 61-72									
ms	MS AMMON, WILFRIED VON et al.: "The dependence of bulk defects on the axial temperature gradient of silicon crystals during Czochralski growth" 2300 JOURNAL OF CRYSTAL GROWTH 151 (1995) June I, Nos. 3/4, Amersterdam, NL, Pages 273-277								
Examiner /Matthew Song/				Date Considered 08/09/2006 9/20/2006					
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not									